

2SK1532

Silicon N Channel Junction FET
Low Frequency Amplifier, Analog Switching

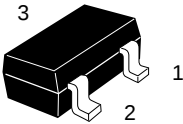
Features

- Suitable for low frequency amplifier, variable resistance and analog switching circuit of audio equipment.
- Compact packages.

Table 1 Absolute Maximum Ratings
(Ta = 25°C)

Item	Symbol	Rating	Unit
Gate to drain voltage	V _{GDO}	-50	V
Gate to source voltage	V _{GSS}	-50	V
Drain current	I _D	10	mA
Channel power dissipation	P _{ch}	100	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

CMPAK



- 1. Drain
- 2. Source
- 3. Gate

Table 2 Electrical Characteristics (Ta = 25°C)

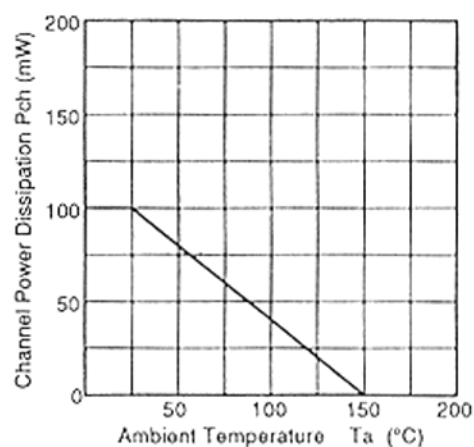
Item	Symbol	Min	Typ	Max	Unit	Test condition
Gate to source breakdown voltage	V _{(BR)GSS}	-50	—	—	V	I _G = -100 μA, V _{DS} = 0
Gate cutoff current	I _{GSS}	—	—	-10	nA	V _{GS} = -30 V, V _{DS} = 0
Drain current	I _{DSS} *	0.6	—	6.5	mA	V _{DS} = 15 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	-0.4	—	-5	V	V _{DS} = 15 V, I _D = 0.1 μA
Forward transfer admittance	y _{fs}	1.0	—	—	mS	V _{DS} = 15 V, V _{GS} = 0, f = 1 kHz
Input capacitance	C _{iss}	—	5.2	—	pF	V _{DS} = 15 V, V _{GS} = 0, f = 1 kHz
Output capacitance	C _{oss}	—	1.5	—	pF	V _{DS} = 15 V, V _{GS} = 0, f = 1 kHz

* The 2SK1532 is grouped by I_{DSS} as follows.

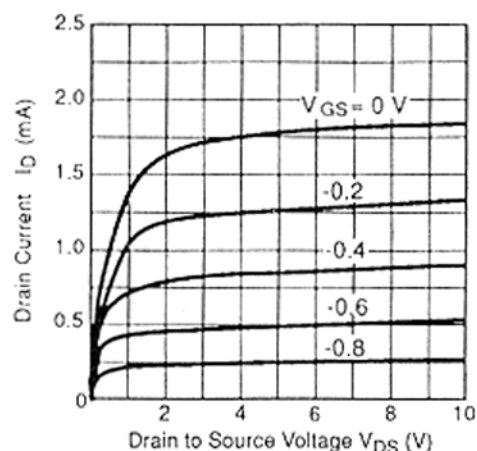
Grade	B	C	D
Mark	XDB	XDC	XDD
I _{DSS} (mA)	0.6 to 1.4	1.2 to 3.0	2.6 to 6.5

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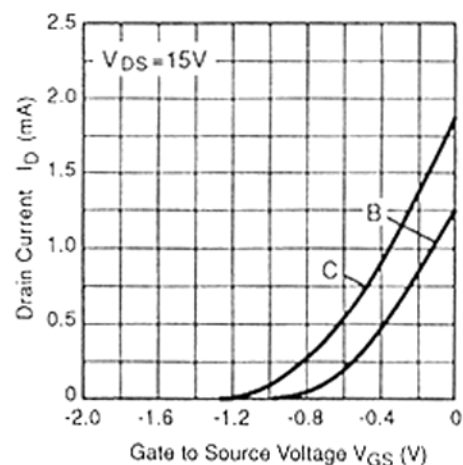
Maximum channel dissipation curve



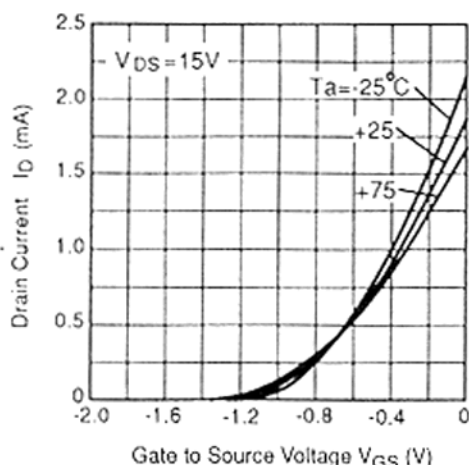
Typical output characteristics

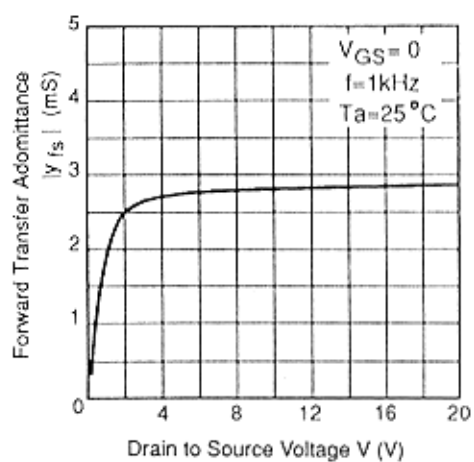
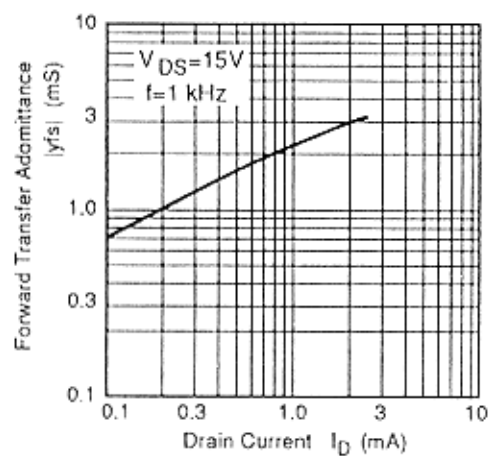


Typical transfer characteristics (1)



Typical transfer characteristics (2)



Forward transfer admittance
vs. drain to source voltageForward transfer admittance
vs. drain current

Capacitance vs. drain to source voltage

